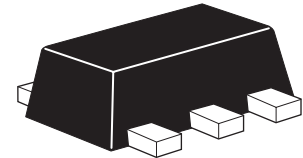


ZXTN25040DZ

40V, SOT89, NPN medium power transistor

Summary

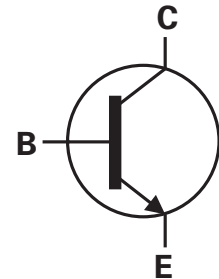
$BV_{CEX} > 130V$
 $BV_{CEO} > 40V$
 $BV_{ECO} > 6V$
 $I_{C(cont)} = 5A$
 $V_{CE(sat)} < 60mV @ 1A$
 $R_{CE(sat)} = 38m\Omega$
 $P_D = 2.4W$



Complementary part number ZXTP25040DZ

Description

Packaged in the SOT89 outline this new low saturation 40V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

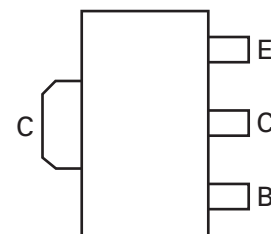


Features

- Extremely low equivalent on resistance; $R_{CE(sat)} = 36m\Omega$ at 5A
- 5A continuous current
- Up to 10 amps peak current
- Very low saturation voltages
- Excellent h_{FE} characteristics
- 6V reverse blocking capability

Applications

- Emergency lighting circuits
- Motor driving (including DC fans)
- Solenoid, relay and actuator drivers
- DC-DC modules
- Backlight inverters
- Power switches
- MOSFET gate drivers



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25040DZTA	7	12	1000

Device marking

1C8

ZXTN25040DZ

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	130	V
Collector-emitter voltage (forward blocking)	V_{CEX}	130	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	6	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current ^(b)	I_C	5	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	10	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P_D	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	1.8	W
Linear derating factor		14.4	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$	P_D	2.4	W
Linear derating factor		19.2	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	P_D	4.46	W
Linear derating factor		35.7	mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	117	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	68	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	51	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	28	°C/W

NOTES:

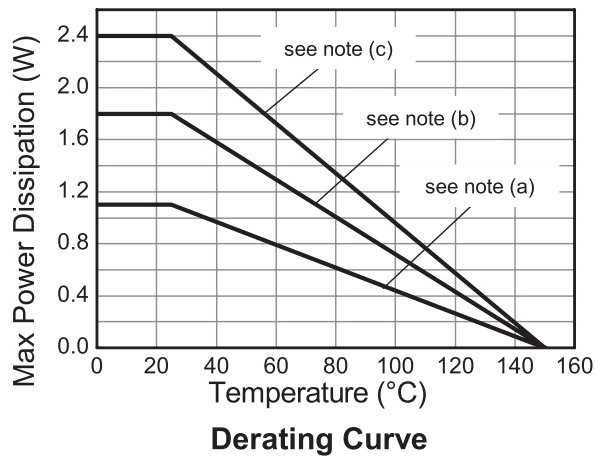
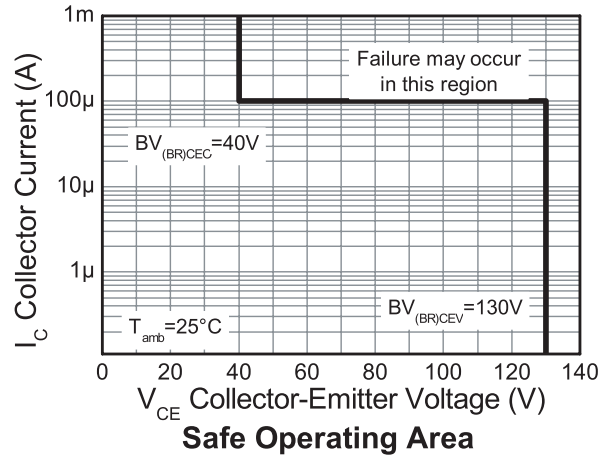
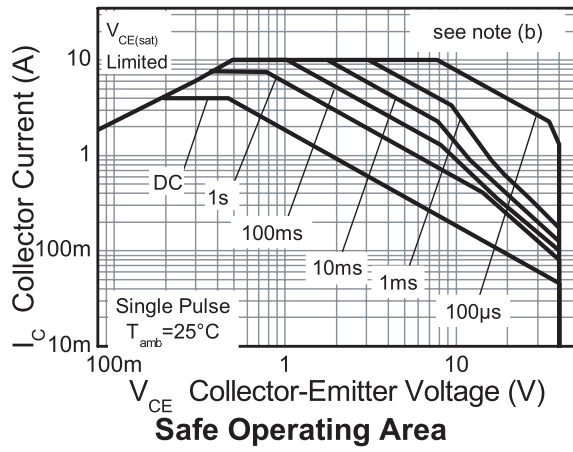
(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

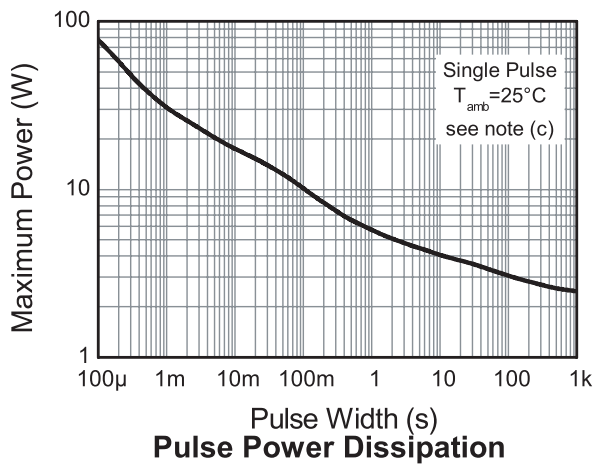
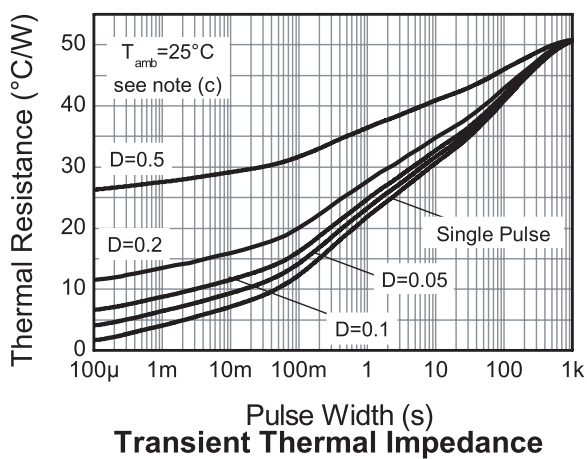
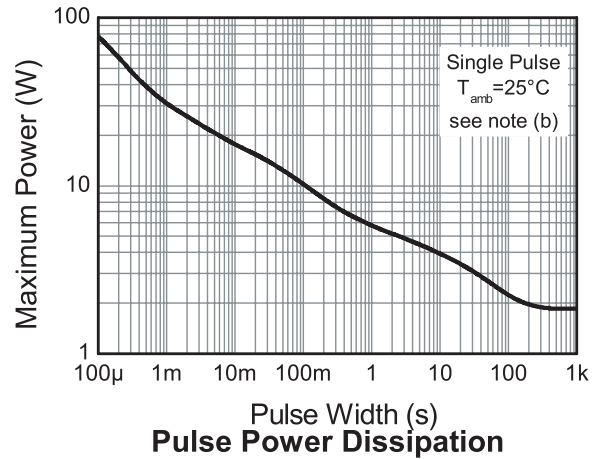
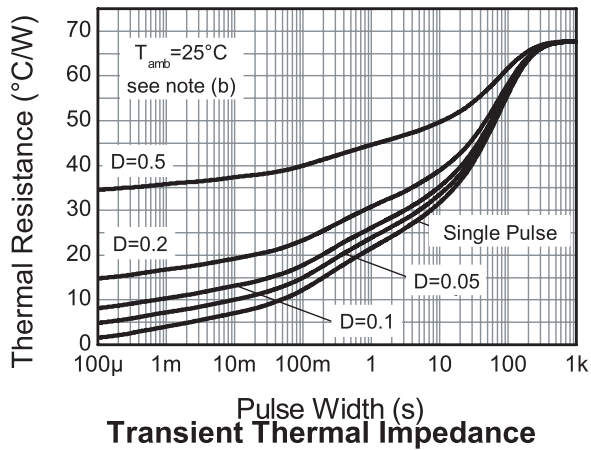
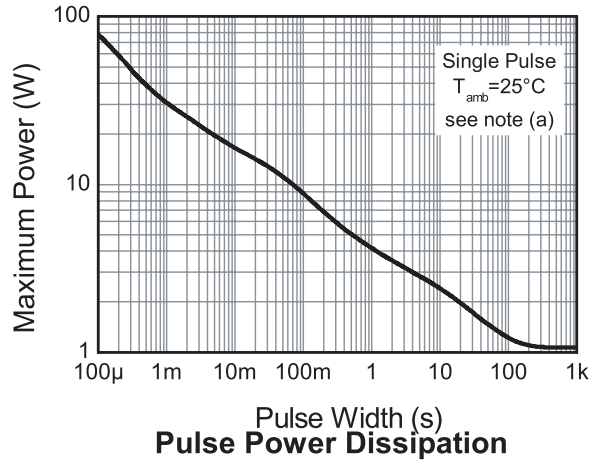
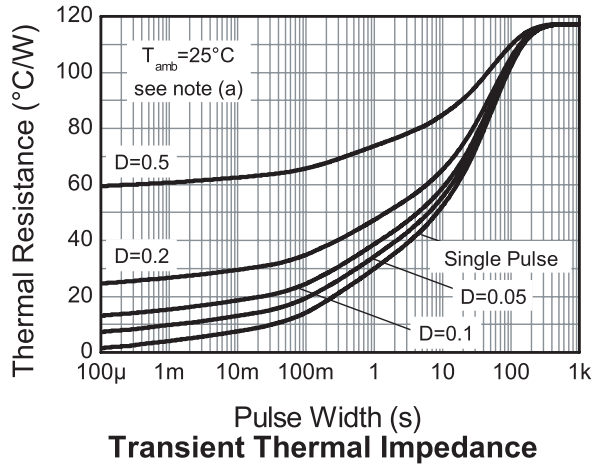
(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

Thermal characteristics



Thermal characteristics (cont.)



ZXTN25040DZ

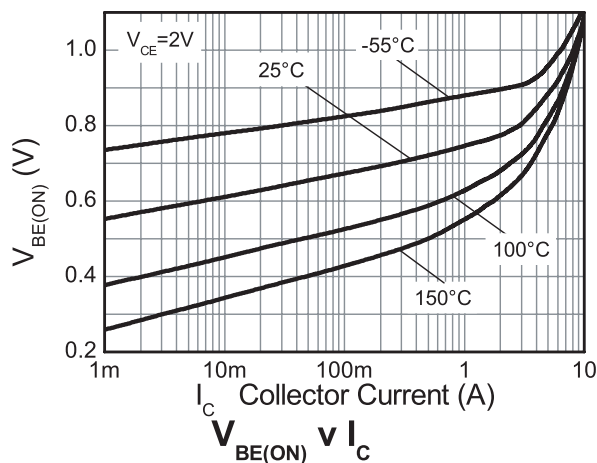
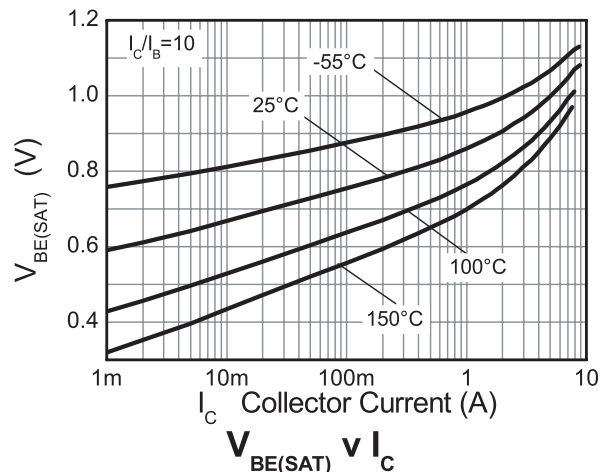
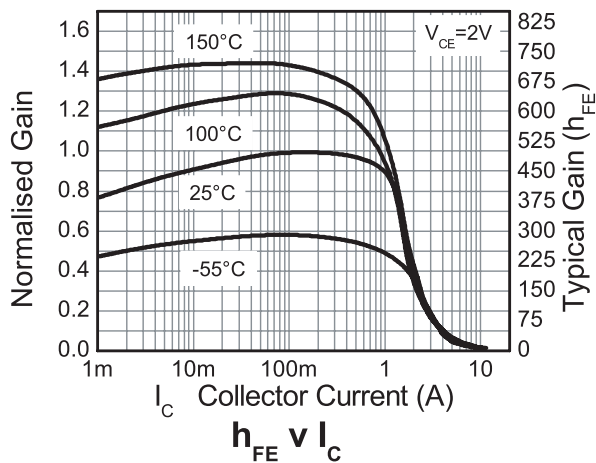
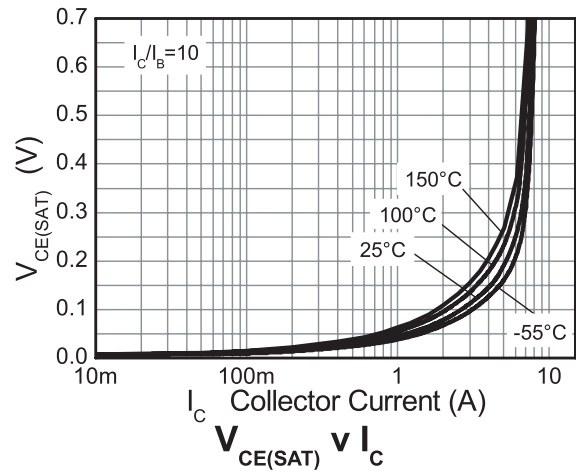
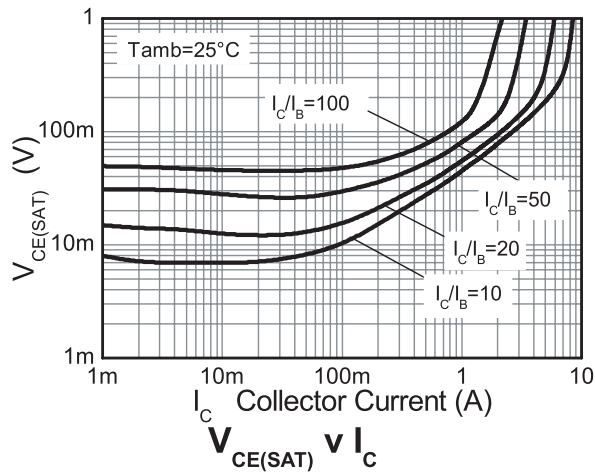
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	130	170		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	130	170		V	$V_{CE} = 130\text{V}; R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	40	63		V	$I_C = 10\text{mA}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	7	8.3		V	$I_E = 100\mu\text{A}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	7.4		V	$I_E = 100\mu\text{A}, R_{BC} \leq 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	6	7.4		V	$I_E = 100\mu\text{A}$,
Collector-base cut-off current	I_{CBO}		<1	50 20	nA μA	$V_{CB} = 100\text{V}$ $V_{CB} = 100\text{V}, T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = 100\text{V}; R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter-base cut-off current	I_{EBO}		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		50 125 140 190	60 215 215 260	mV mV mV mV	$I_C = 1\text{A}, I_B = 100\text{mA}^{(*)}$ $I_C = 1\text{A}, I_B = 10\text{mA}^{(*)}$ $I_C = 2\text{A}, I_B = 40\text{mA}^{(*)}$ $I_C = 5\text{A}, I_B = 500\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		1000	1100	mV	$I_C = 5\text{A}, I_B = 500\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		910	1000	mV	$I_C = 5\text{A}, V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	300 300 20	450 450 40 10	900		$I_C = 10\text{mA}, V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}, V_{CE} = 2\text{V}^{(*)}$ $I_C = 5\text{A}, V_{CE} = 2\text{V}^{(*)}$ $I_C = 10\text{A}, V_{CE} = 2\text{V}^{(*)}$
Transition frequency	f_T		190		MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		11.7	20	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}^{(*)}$
Delay time	t_d		64		ns	$V_{CC} = 10\text{V}$ $I_C = 1\text{A}$, $I_{B1} = I_{B2} = 10\text{mA}$
Rise time	t_r		108		ns	
Storage time	t_s		428		ns	
Fall time	t_f		130		ns	

NOTES:

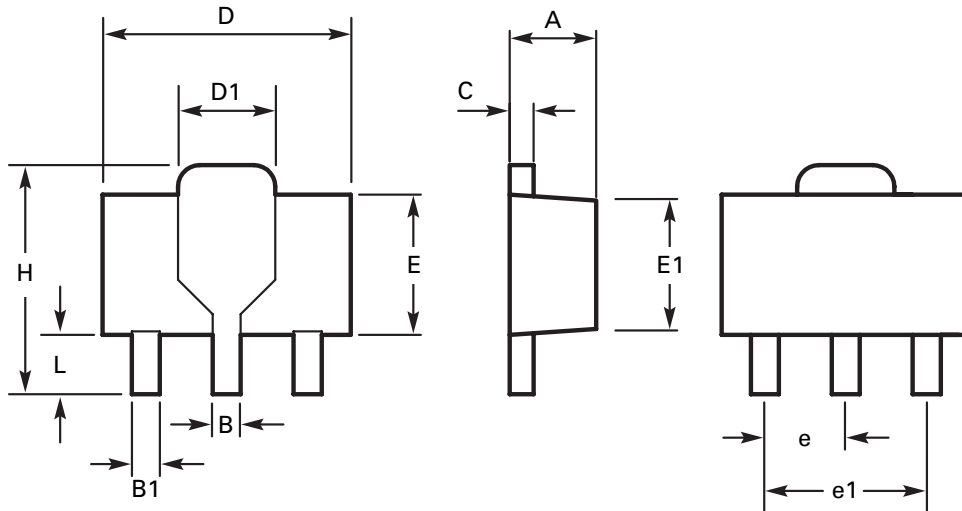
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTN25040DZ

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E1	2.13	2.29	0.084	0.090
B	0.44	0.56	0.017	0.022	e	1.50 BSC		0.059 BSC	
B1	0.36	0.48	0.014	0.019	e1	3.00 BSC		0.118 BSC	
C	0.35	0.44	0.014	0.019	H	3.94	4.25	0.155	0.167
D	4.40	4.60	0.173	0.181	L	0.89	1.20	0.155	0.167
E	2.29	2.60	0.090	0.102		-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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